

# Third Quarter 2024 Financial Results Conference Call

Supporting Slides

November 13, 2024



# Safe Harbor

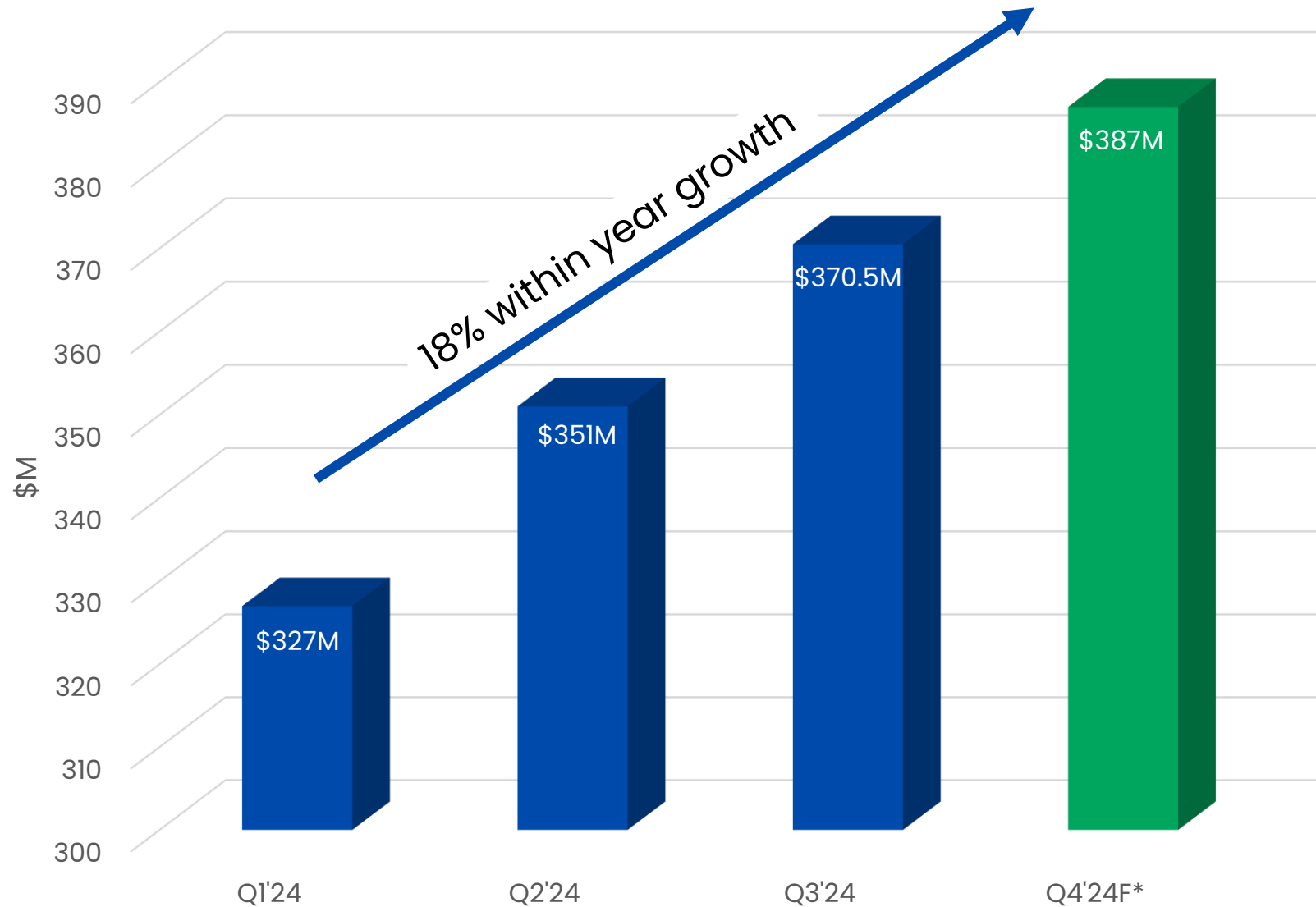
This presentation contains forward-looking statements within the meaning of the “safe harbor” provisions of the Private Securities Litigation Reform Act of 1995. These statements are based on management’s current expectations and beliefs and are subject to a number of risks, uncertainties and assumptions that could cause actual results to differ materially from those described in the forward-looking statements. All statements other than statements of historical fact are statements that could be deemed forward-looking statements.

For example, statements regarding expected (i) customer demand, (ii) utilization and cross utilization of our Fabs, (iii) demand from our end markets, (iv) market and technology trends, and (v) results regarding revenues, cash flow, margins and net profits are all forward-looking statements. Actual results may differ materially from those projected or implied by such forward-looking statements due to various risks and uncertainties applicable to Tower Semiconductor’s business as described in the reports filed by Tower Semiconductor Ltd. (“Tower”) with the Securities and Exchange Commission (the “SEC”) and the Israel Securities Authority (“ISA”), including the risks identified under the heading "Risk Factors" in Tower’s most recent filings on Forms 20-F and 6-K. No assurances can be given that any of the events anticipated by the forward-looking statements will transpire or occur, or if any of them do, what impact they will have on the results of operations or financial condition of Tower Semiconductor.

In addition, some of the financial information in this presentation, is non-GAAP financial measures, including, but not limited to, EBITDA, Cash, debt and Net Cash. These non-GAAP financial measures have the same definition as appear in our previously filed quarterly financial results related announcements and/ or other public filings.

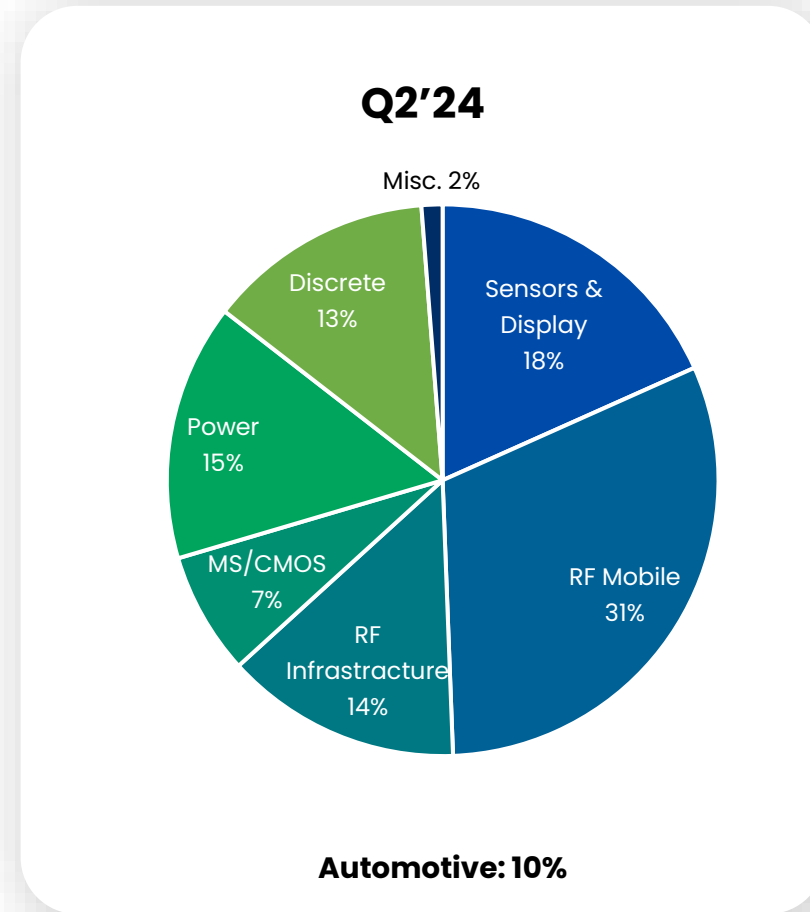
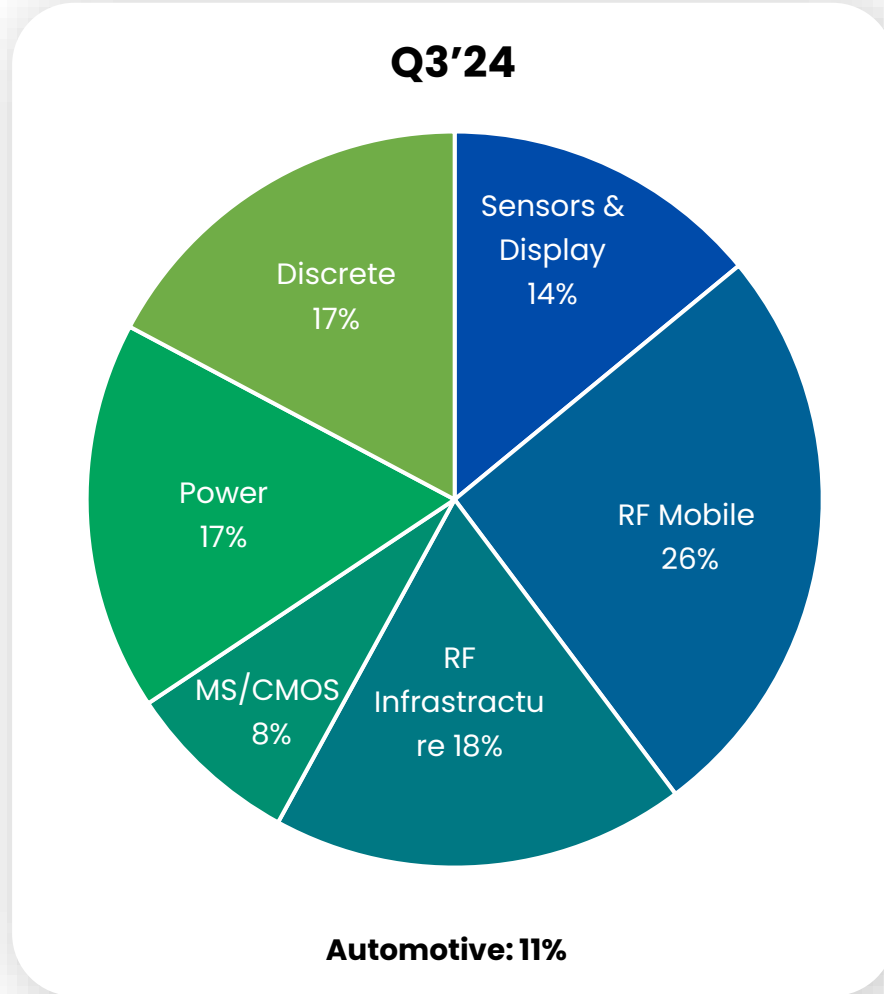
Tower Semiconductor is providing this information as of the date of this presentation and expressly disclaims any obligation to update any of the forward-looking statements or other information contained in this presentation as a result of new information, future events or otherwise.

# 2024 Revenue Performance and Guidance



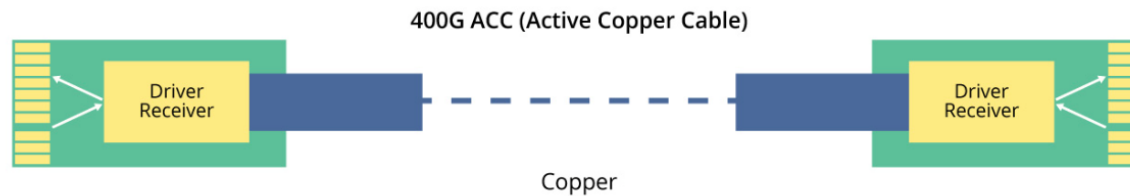
\* Q4'24 revenue represents mid-range guidance

# Q3 2024 Revenue Breakdown by Technology

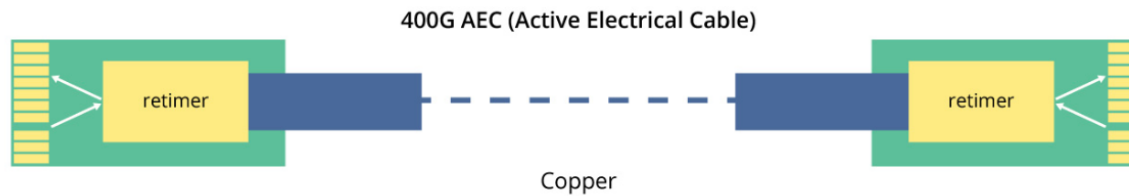


# Active Copper Cables

- Active Copper Cables: with SiGe based linear equalizers (redrivers)

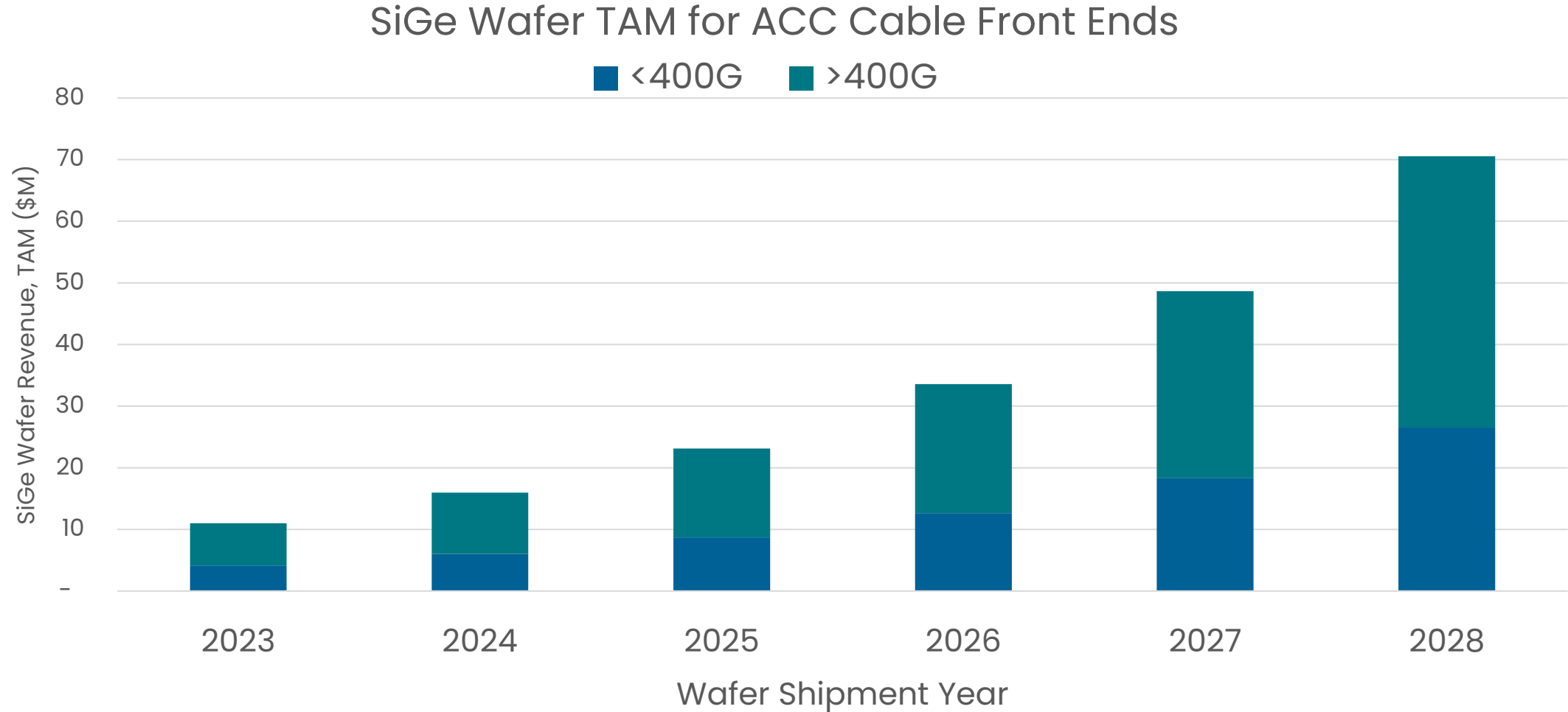


- Active Electrical Cables: with SiGe based analog clock and data recovery (retimers)



Source: FS.com, Cadence

# ACC: 6X Growth in SiGe Wafer TAM from '23 to '28 Dominated by >400G Networking Cables



Sources: Lightcounting '22, '23 and company estimates

# Tower's 65nm BCD fits Power ICs in Smartphone

	Est. 12" Wafer TAM [KWPM]	65nm 5V BCD Platform (PMK)	65nm 3.3V BCD Platform (PML)
<b>Other</b> <i>Regulators, Haptic drv., MS IC</i>	<b>22</b>	<ul style="list-style-type: none"> <li>✓ Wide offering for different ICs</li> <li>✓ Rich Analog &amp; power 5V based</li> </ul>	<ul style="list-style-type: none"> <li>✓ Wide offering for different ICs</li> <li>✓ Rich Analog &amp; power 3.3V based</li> </ul>
<b>Audio</b> <i>Audio Amplifiers</i>	<b>28</b>	<ul style="list-style-type: none"> <li>✓ High digital content for improved audio amplifiers sound</li> <li>✓ Advance 5V analog for analog audio amplifiers</li> <li>✓ High voltage for high power sound</li> </ul>	<ul style="list-style-type: none"> <li>✓ High digital content for improved audio amplifiers sound</li> <li>✓ Advance 3.3V analog for high audio quality with noise</li> <li>✓ High voltage for high power sound</li> </ul>
<b>Charge IC</b> <i>USB-C &amp; Wireless</i> <b>BMS IC</b>	<b>60</b>	<ul style="list-style-type: none"> <li>✓ 65nm Digital Density &amp; IPs for large type of charger ICs</li> <li>✓ Advance 5V Analog for most USB-C inputs</li> <li>✓ High Voltage for fast charging supporting latest std.</li> </ul>	<ul style="list-style-type: none"> <li>✓ 65nm Digital Density &amp; IPs</li> <li>✓ Advance 5V Analog</li> <li>✓ High Voltage for fast charging</li> </ul>
<b>PMIC</b> <i>Multi channel power IC</i>	<b>121</b>	<ul style="list-style-type: none"> <li>✓ Advanced Analog 1.2V &amp; 5V</li> <li>✓ Digital core 65nm based for multi channel sync.</li> <li>✓ Wide voltage scale power devices for different PMICs (Display, SoC, Camera,..)</li> </ul>	<ul style="list-style-type: none"> <li>✓ 3.3V Analog centric for advance power mentoring</li> <li>✓ High digital content using 65nm core &amp; rich IPs</li> <li>✓ Wide voltage scale power devices for different PMIC (Display, SoC, Camera,..)</li> </ul>

Typical smart phone  
Power ICs content

# 65nm BCD Modularity

## Widest Coverage

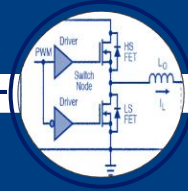
Power & Analog applications with best-in-class FOMs

### 3.3V or 5V Mixed Signal



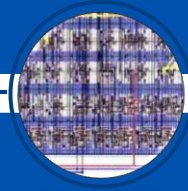
3.3V or 5V Mixed Signal  
Rich device list  
NVM solutions  
IOs & digital Lib  
ESD solutions

### Power Device



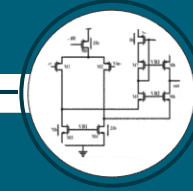
Best in class LDMOS  
DEMOS options  
Voltage scale options  
Excellent Isolation  
HV ESD solutions

### 1.2V Core



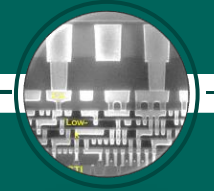
Standard cell libraries  
Memory compilers  
1.2V IOs  
NVM options

### Analog



1.2V/3.3V/5V Analog  
Sub-threshold design  
Aging models  
Rich passives devices

### BEOL



2 to 6 level metal  
Top thick Cu  
0.9 $\mu$ m/3.3 $\mu$ m/2x3.3 $\mu$ m

Cost-performance excellence

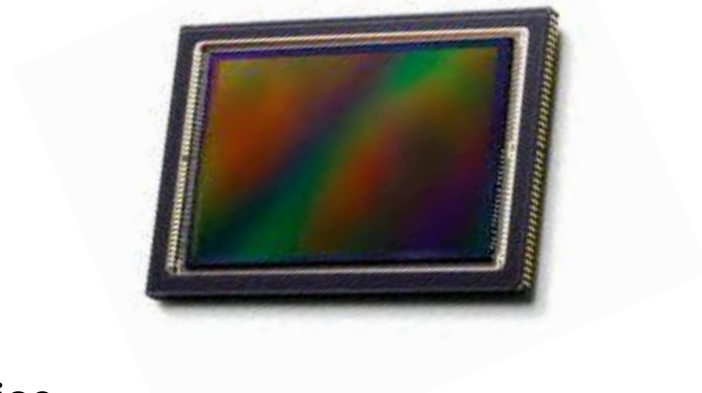
Feature rich PDK



# High Resolution Industrial & Digital Photography

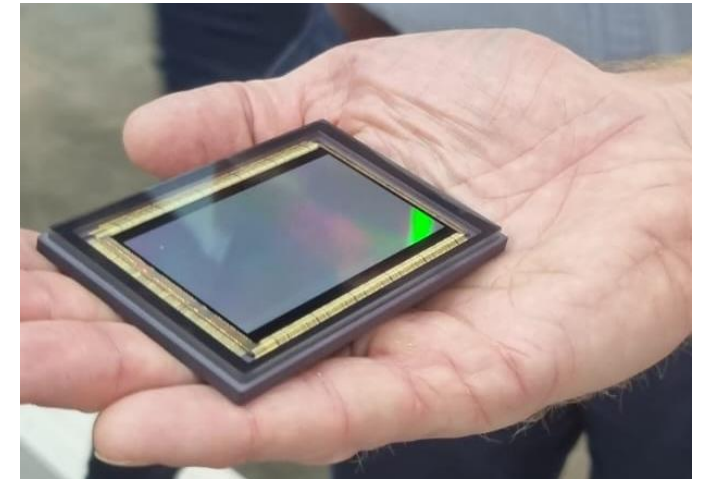
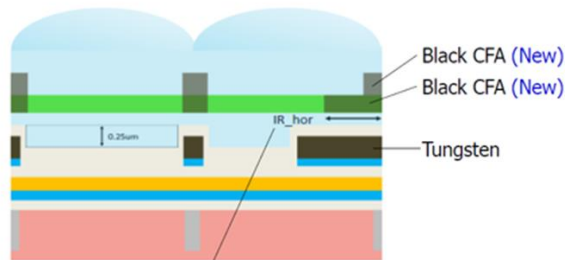


- Tower Semiconductor offer :
  - 300mm 65nm process, Back Side Illuminated / stacked



  
**VISION**

- Unique Technologies:
  - 300mm Stitching and Stacking capabilities
  - Low noise Charge domain global shutter for next generation DSLR/MLC
  - High Dynamic Range pixels
  - New autofocus pixels on BSI sensor



# Micro Displays – OLED On Silicon (OLEDoS)

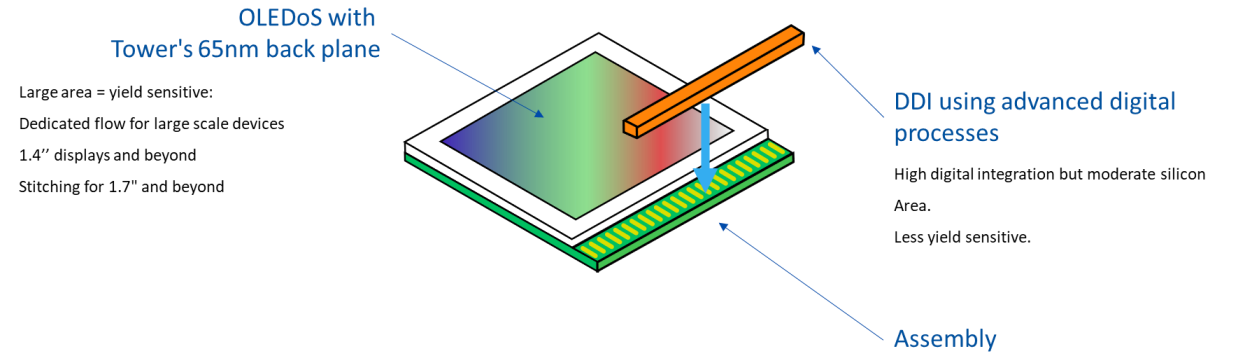


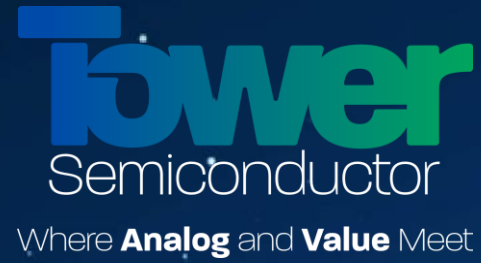
- Wafer revenue, SAM and Market share
- CAGR : 50%

- Unique Technology :
  - Dedicated devices for OLEDoS:
    - Ultra low leakage dedicated transistors
    - High density, in-pixel capacitors
  - High Yield flow for large dies

- Tower Semiconductor offer :
  - 300mm 65nm process for OLED CMOS backplanes

2 Chip solution with dedicated flows :





# Thank You

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